

Panasonic 1 ICP SiNx etching CF4 O2

Data provided by Jon Barton

- For in-house PECVD Oxide. LPCVD oxide from outside will have lower rates.

- ICP 500W

- Bias Power varies

- Pressure Varied

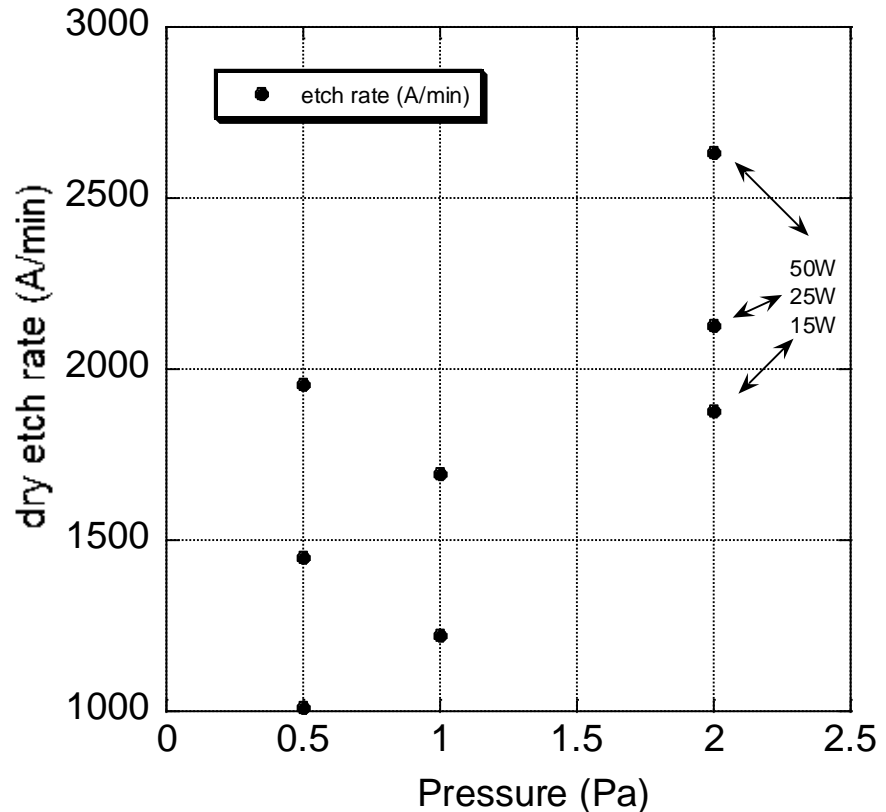
- 50 sccm CF4

- 5 sccm O2

- Very fast etch rates

- About 1:1 etch ratio with PR

**ICP Etch Rates of PECVD Silicon Oxynitride
Source Power 500W**



Slowing down the rate

- For in-house PECVD Oxide. LPCVD oxide from outside will have lower rates.
- ICP Varied
- Bias Power 25W
- 50 sccm CF4
- 5 sccm O2
- 1 Pa pressure

